

isc Triacs

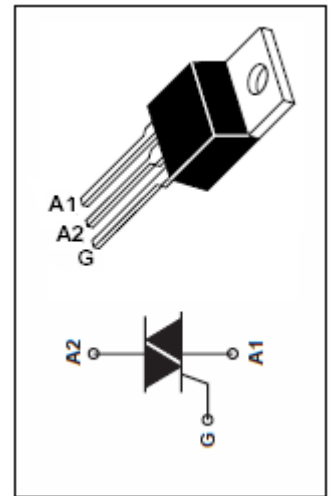
TIC216M

FEATURES

- With TO-220 package
- Sensitive Gate Triacs
- Glass Passivated
- Max I_{GT} of 5 mA (Quadrants 1~3)

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	MIN	UNIT
V_{DRM}	Repetitive peak off-state voltage	600	V
V_{RRM}	Repetitive peak reverse voltage	600	V
$I_{T(RMS)}$	RMS on-state current (full sine wave) $T_C=70^{\circ}C$	6	A
I_{TSM}	Non-repetitive peak on-state current	60	A
T_j	Operating junction temperature	110	$^{\circ}C$
T_{stg}	Storage temperature	-45~150	$^{\circ}C$
$R_{th(j-c)}$	Thermal resistance, junction to case	2.5	$^{\circ}C/W$
$R_{th(j-a)}$	Thermal resistance, junction to ambient	62.5	$^{\circ}C/W$



ELECTRICAL CHARACTERISTICS ($T_C=25^{\circ}C$ unless otherwise specified)

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
I_{DRM}	Repetitive peak off-state current	$V_D=V_{DRM}, T_C=110^{\circ}C$	2.0	mA
I_{GT}	Gate trigger current	I	$V_{supply} = 12 V\ddagger; R_L = 10 \Omega; t_{p(g)} > 20 \mu s$	5
		II		5
		III		5
		IV		10
I_H	Holding current	$V_{supply} = 12 V\ddagger, I_G = 0$ initial $I_{TM} = 100mA$	30	mA
V_{GT}	Gate trigger voltage	I	$V_{supply} = 12 V\ddagger; R_L = 10 \Omega; t_{p(g)} > 20 \mu s$	2.2
		II		2.2
		III		2.2
		IV		3.0
V_{TM}	On-state voltage	$I_T = 8.4A; I_G = 50mA$	1.7	V